

# STARPOWER

SEMICONDUCTOR

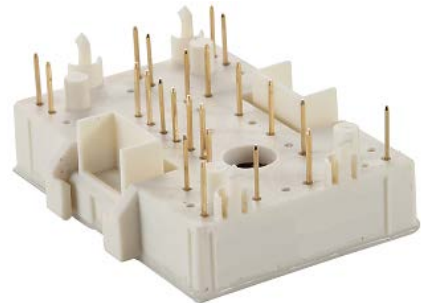
**IGBT**

## GD10PJY120L1S

**1200V/10A PIM in one-package**

### General Description

STARPOWER IGBT Power Module provides ultra low conduction loss as well as short circuit ruggedness. They are designed for the applications such as general inverters and UPS.



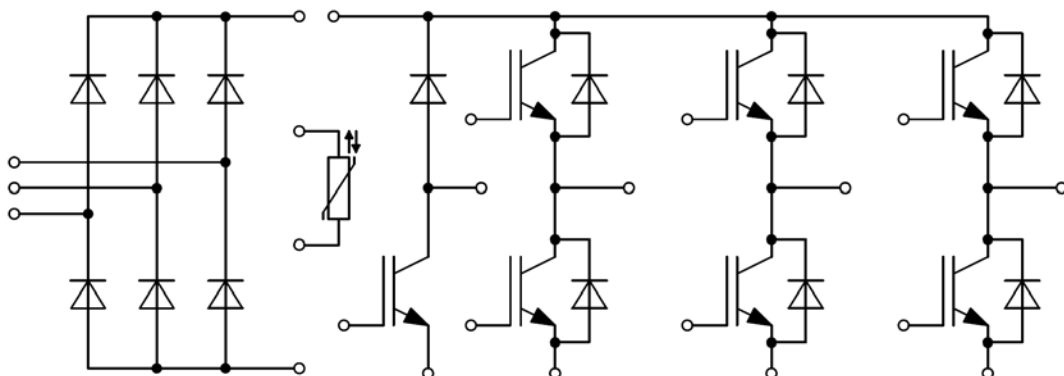
### Features

- Low  $V_{CE(sat)}$  Trench IGBT technology
- 10 $\mu$ s short circuit capability
- $V_{CE(sat)}$  with positive temperature coefficient
- Maximum junction temperature 175°C
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated heatsink using DBC technology

### Typical Applications

- Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

### Equivalent Circuit Schematic



**Absolute Maximum Ratings**  $T_C=25^{\circ}\text{C}$  unless otherwise noted**IGBT-inverter**

Symbol	Description	Value	Unit
$V_{CES}$	Collector-Emitter Voltage	1200	V
$V_{GES}$	Gate-Emitter Voltage	$\pm 20$	V
$I_C$	Collector Current @ $T_C=25^{\circ}\text{C}$	20	A
	@ $T_C=100^{\circ}\text{C}$	10	
$I_{CM}$	Pulsed Collector Current $t_p=1\text{ms}$	20	A
$P_D$	Maximum Power Dissipation @ $T_j=175^{\circ}\text{C}$	110	W

**Diode-inverter**

Symbol	Description	Value	Unit
$V_{RRM}$	Repetitive Peak Reverse Voltage	1200	V
$I_F$	Diode Continuous Forward Current	10	A
$I_{FM}$	Diode Maximum Forward Current $t_p=1\text{ms}$	20	A

**Diode-rectifier**

Symbol	Description	Value	Unit
$V_{RRM}$	Repetitive Peak Reverse Voltage	1600	V
$I_O$	Average Output Current 50Hz/60Hz,sine wave	10	A
$I_{FSM}$	Surge Forward Current $V_R=0\text{V}, t_p=10\text{ms}, T_j=45^{\circ}\text{C}$	270	A
$I^2t$	$I^2t$ -value, $V_R=0\text{V}, t_p=10\text{ms}, T_j=45^{\circ}\text{C}$	360	$\text{A}^2\text{s}$

**IGBT-brake**

Symbol	Description	Value	Unit
$V_{CES}$	Collector-Emitter Voltage	1200	V
$V_{GES}$	Gate-Emitter Voltage	$\pm 30$	V
$I_C$	Collector Current @ $T_C=25^{\circ}\text{C}$	20	A
	@ $T_C=100^{\circ}\text{C}$	10	
$I_{CM}$	Pulsed Collector Current $t_p=1\text{ms}$	20	A
$P_D$	Maximum Power Dissipation @ $T_j=175^{\circ}\text{C}$	110	W

**Diode-brake**

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$V_{RRM}$	Repetitive Peak Reverse Voltage	1200	V
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**Module**

Symbol	Description	Value	Unit
$T_{jmax}$	Maximum Junction Temperature(inverter,brake)	175	$^{\circ}\text{C}$
	Maximum Junction Temperature (rectifier)	150	
$T_{jop}$	Operating Junction Temperature	-40 to +150	$^{\circ}\text{C}$
$T_{STG}$	Storage Temperature Range	-40 to +125	$^{\circ}\text{C}$
$V_{ISO}$	Isolation Voltage RMS,f=50Hz,t=1min	2500	V

**IGBT-inverter Characteristics**  $T_C=25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=10\text{A}, V_{GE}=15\text{V}, T_j=25^\circ\text{C}$		1.65	2.10	V	
		$I_C=10\text{A}, V_{GE}=15\text{V}, T_j=125^\circ\text{C}$		1.95			
		$I_C=10\text{A}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}$		2.00			
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=0.25\text{mA}, V_{CE}=V_{GE}, T_j=25^\circ\text{C}$	5.2	6.0	6.8	V	
$I_{CES}$	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$			1.0	mA	
$I_{GES}$	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^\circ\text{C}$			400	nA	
$R_{Gint}$	Internal Gate Resistance			0		$\Omega$	
$C_{ies}$	Input Capacitance	$V_{CE}=30\text{V}, f=1\text{MHz}, V_{GE}=0\text{V}$		0.90		nF	
$C_{res}$	Reverse Transfer Capacitance				0.03		nF
$Q_G$	Gate Charge	$V_{GE}=-15\dots+15\text{V}$		0.06		$\mu\text{C}$	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=10\text{A}, R_G=82\Omega, V_{GE}=\pm 15\text{V}, T_j=25^\circ\text{C}$		188		ns	
$t_r$	Rise Time			45		ns	
$t_{d(off)}$	Turn-Off Delay Time			209		ns	
$t_f$	Fall Time			353		ns	
$E_{on}$	Turn-On Switching Loss			1.53		mJ	
$E_{off}$	Turn-Off Switching Loss			0.63		mJ	
$t_{d(on)}$	Turn-On Delay Time		$V_{CC}=600\text{V}, I_C=10\text{A}, R_G=82\Omega, V_{GE}=\pm 15\text{V}, T_j=125^\circ\text{C}$		184		ns
$t_r$	Rise Time				42		ns
$t_{d(off)}$	Turn-Off Delay Time			226		ns	
$t_f$	Fall Time			521		ns	
$E_{on}$	Turn-On Switching Loss			1.90		mJ	
$E_{off}$	Turn-Off Switching Loss			1.00		mJ	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=10\text{A}, R_G=82\Omega, V_{GE}=\pm 15\text{V}, T_j=150^\circ\text{C}$			182		ns
$t_r$	Rise Time				42		ns
$t_{d(off)}$	Turn-Off Delay Time			239		ns	
$t_f$	Fall Time			548		ns	
$E_{on}$	Turn-On Switching Loss			2.11		mJ	
$E_{off}$	Turn-Off Switching Loss			1.10		mJ	
$I_{SC}$	SC Data		$t_p \leq 10\mu\text{s}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}, V_{CC}=900\text{V}, V_{CEM} \leq 1200\text{V}$		40		A

**Diode-inverter Characteristics**  $T_C=25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_F$	Diode Forward Voltage	$I_F=10\text{A}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$		1.85	2.30	V
		$I_F=10\text{A}, V_{GE}=0\text{V}, T_j=125^\circ\text{C}$		2.05		
		$I_F=10\text{A}, V_{GE}=0\text{V}, T_j=150^\circ\text{C}$		2.10		
$Q_r$	Recovered Charge	$V_R=600\text{V}, I_F=10\text{A},$ $-di/dt=260\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=25^\circ\text{C}$		0.5		$\mu\text{C}$
$I_{RM}$	Peak Reverse Recovery Current			13		A
$E_{rec}$	Reverse Recovery Energy			0.28		mJ
$Q_r$	Recovered Charge	$V_R=600\text{V}, I_F=10\text{A},$ $-di/dt=260\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=125^\circ\text{C}$		0.7		$\mu\text{C}$
$I_{RM}$	Peak Reverse Recovery Current			14		A
$E_{rec}$	Reverse Recovery Energy			0.48		mJ
$Q_r$	Recovered Charge	$V_R=600\text{V}, I_F=10\text{A},$ $-di/dt=260\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=150^\circ\text{C}$		0.8		$\mu\text{C}$
$I_{RM}$	Peak Reverse Recovery Current			15		A
$E_{rec}$	Reverse Recovery Energy			0.58		mJ

**Diode-rectifier Characteristics**  $T_C=25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_F$	Diode Forward Voltage	$I_F=10\text{A}, T_j=150^\circ\text{C}$		0.88		V
$I_R$	Reverse Current	$T_j=150^\circ\text{C}, V_R=1600\text{V}$			1.0	mA

**IGBT-brake Characteristics**  $T_C=25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=10\text{A}, V_{GE}=15\text{V}, T_j=25^\circ\text{C}$		1.70	2.15	V	
		$I_C=10\text{A}, V_{GE}=15\text{V}, T_j=125^\circ\text{C}$		1.95			
		$I_C=10\text{A}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}$		2.00			
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=0.40\text{mA}, V_{CE}=V_{GE}, T_j=25^\circ\text{C}$	5.0	5.5	6.5	V	
$I_{CES}$	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$			1.0	mA	
$I_{GES}$	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^\circ\text{C}$			400	nA	
$R_{Gint}$	Internal Gate Resistance			0		$\Omega$	
$C_{ies}$	Input Capacitance	$V_{CE}=30\text{V}, f=1\text{MHz}, V_{GE}=0\text{V}$		0.90		nF	
$C_{res}$	Reverse Transfer Capacitance				0.03		nF
$Q_G$	Gate Charge	$V_{GE}=-15\dots+15\text{V}$		0.06		$\mu\text{C}$	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=10\text{A}, R_G=82\Omega, V_{GE}=\pm 15\text{V}, T_j=25^\circ\text{C}$		188		ns	
$t_r$	Rise Time			45		ns	
$t_{d(off)}$	Turn-Off Delay Time			209		ns	
$t_f$	Fall Time			353		ns	
$E_{on}$	Turn-On Switching Loss			1.53		mJ	
$E_{off}$	Turn-Off Switching Loss			0.63		mJ	
$t_{d(on)}$	Turn-On Delay Time		$V_{CC}=600\text{V}, I_C=10\text{A}, R_G=82\Omega, V_{GE}=\pm 15\text{V}, T_j=125^\circ\text{C}$		184		ns
$t_r$	Rise Time				42		ns
$t_{d(off)}$	Turn-Off Delay Time			226		ns	
$t_f$	Fall Time			521		ns	
$E_{on}$	Turn-On Switching Loss			1.90		mJ	
$E_{off}$	Turn-Off Switching Loss			1.00		mJ	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=10\text{A}, R_G=82\Omega, V_{GE}=\pm 15\text{V}, T_j=150^\circ\text{C}$			182		ns
$t_r$	Rise Time				42		ns
$t_{d(off)}$	Turn-Off Delay Time			239		ns	
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$E_{on}$	Turn-On Switching Loss			2.11		mJ	
$E_{off}$	Turn-Off Switching Loss			1.10		mJ	
$I_{SC}$	SC Data		$t_p \leq 10\mu\text{s}, V_{GE}=15\text{V}, T_j=150^\circ\text{C}, V_{CC}=900\text{V}, V_{CEM} \leq 1200\text{V}$		40		A

**Diode-brake Characteristics**  $T_C=25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_F$	Diode Forward Voltage	$I_F=10\text{A}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$		1.85	2.30	V
		$I_F=10\text{A}, V_{GE}=0\text{V}, T_j=125^\circ\text{C}$		2.05		
		$I_F=10\text{A}, V_{GE}=0\text{V}, T_j=150^\circ\text{C}$		2.10		
$Q_r$	Recovered Charge	$V_R=600\text{V}, I_F=10\text{A},$ $-di/dt=260\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=25^\circ\text{C}$		0.5		$\mu\text{C}$
$I_{RM}$	Peak Reverse Recovery Current			13		A
$E_{rec}$	Reverse Recovery Energy			0.28		mJ
$Q_r$	Recovered Charge	$V_R=600\text{V}, I_F=10\text{A},$ $-di/dt=260\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=125^\circ\text{C}$		0.7		$\mu\text{C}$
$I_{RM}$	Peak Reverse Recovery Current			14		A
$E_{rec}$	Reverse Recovery Energy			0.48		mJ
$Q_r$	Recovered Charge	$V_R=600\text{V}, I_F=10\text{A},$ $-di/dt=260\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=150^\circ\text{C}$		0.8		$\mu\text{C}$
$I_{RM}$	Peak Reverse Recovery Current			15		A
$E_{rec}$	Reverse Recovery Energy			0.58		mJ

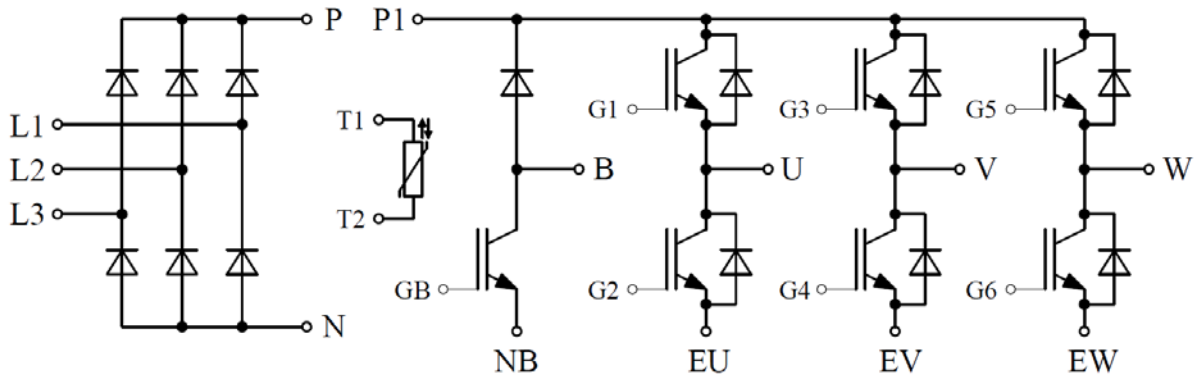
**NTC Characteristics**  $T_C=25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$R_{25}$	Rated Resistance			5.0		$\text{k}\Omega$
$\Delta R/R$	Deviation of $R_{100}$	$T_C=100^\circ\text{C}, R_{100}=493.3\Omega$	-5		5	%
$P_{25}$	Power Dissipation				20.0	mW
$B_{25/50}$	B-value	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15\text{K}))]$		3375		K

**Module Characteristics**  $T_C=25^{\circ}\text{C}$  unless otherwise noted

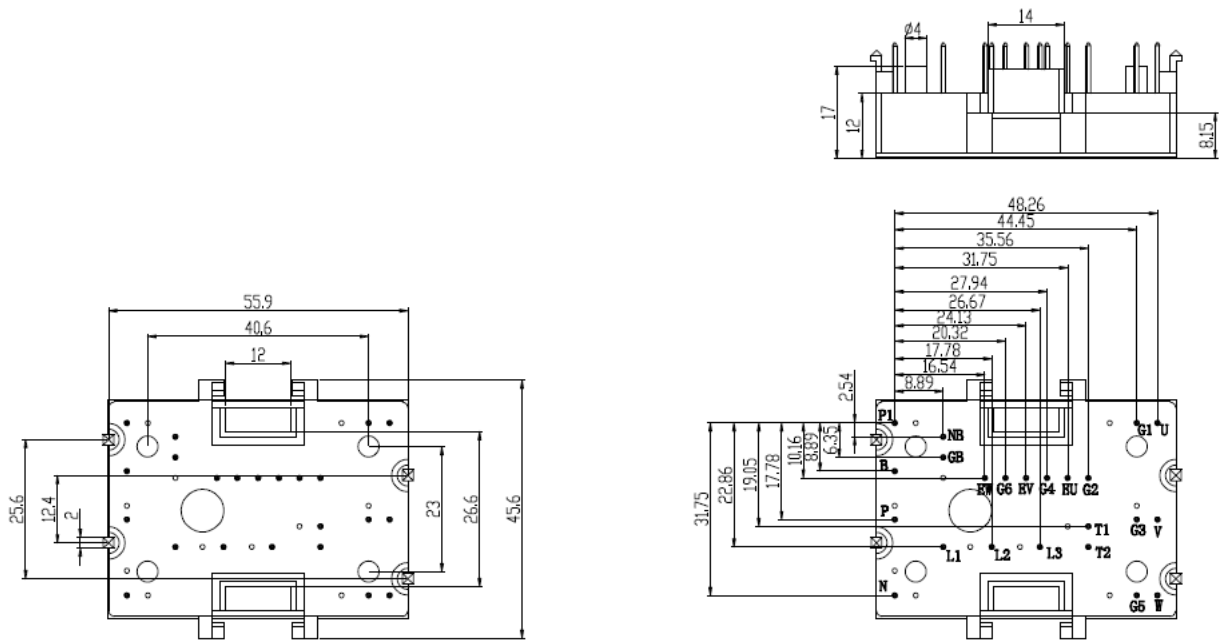
Symbol	Parameter	Min.	Typ.	Max.	Unit
$L_{CE}$	Stray Inductance		40		nH
$R_{CC'+EE'}$ $R_{AA'+CC'}$	Module Lead Resistance, Terminal to Chip		10.0 7.00		m $\Omega$
$R_{thJC}$	Junction-to-Case (per IGBT-inverter)		1.237	1.361	K/W
	Junction-to-Case (per Diode-inverter)		2.223	2.445	
	Junction-to-Case (per Diode-rectifier)		1.326	1.459	
	Junction-to-Case (per IGBT-brake)		1.237	1.361	
	Junction-to-Case (per Diode-brake)		2.223	2.445	
$R_{thCH}$	Case-to-Heatsink (per IGBT-inverter)		0.495		K/W
	Case-to-Heatsink (per Diode-inverter)		0.889		
	Case-to-Heatsink (per Diode-rectifier)		0.530		
	Case-to-Heatsink (per IGBT-brake)		0.495		
	Case-to-Heatsink (per Diode-brake)		0.889		
	Case-to-Heatsink (per Module)		0.030		
F	Mounting Force Per Clamp	40		80	N
G	Weight of Module		36		g

**Circuit Schematic**



**Package Dimensions**

Dimensions in Millimeters





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